

Attorney's Docket No.: 07977-258001

In the claims:

1. (Previously amended) A method of manufacturing a semiconductor device, wherein a material having a tensile stress of  $8 \times 10^9$  dynes/cm<sup>2</sup> or more is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

2. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein said material is formed by LPCVD within a temperature range of between 500 and 900°C.

3. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein said material is formed by LPCVD within a pressure range of between 0.1 and 3 Torr.

4. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein said material is formed by LPCVD with a gas containing chlorine as a material gas.

5 - 6 (Withdrawn)

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7. (Previously amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD within a temperature range of between 500 and 900°C is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

8. (Previously amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD within a pressure range of between 0.1 and 3 Torr is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

9. (Previously amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD with a gas containing chlorine as a material gas is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

10 - 19 (Withdrawn)

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Sub C17  
B1  
20. (Amended) A method of manufacturing a semiconductor device according to claim 4 ~~ex-9~~, wherein the gas containing chlorine is a mixture gas that contains any one of  $\text{SiCl}_4$ ,  $\text{SiH}_2\text{Cl}_2$ ,  $\text{SiCl}_3$ , and  $\text{Si}_2\text{Cl}_6$ .

21 - 59 (Withdrawn)

Please add new claims 60 to 66 as follows:

Sub C17  
60. (New) A method of manufacturing a semiconductor device according to claim 9, wherein the gas containing chlorine is a mixture gas that contains any one of  $\text{SiCl}_4$ ,  $\text{SiH}_2\text{Cl}_2$ ,  $\text{SiCl}_3$ , and  $\text{Si}_2\text{Cl}_6$ .

B2 cont  
61. (New) A method of manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film over a substrate;  
forming a material having a tensile stress of  $8 \times 10^9$  dynes/cm<sup>2</sup> or more in contact with the semiconductor film to getter an impurity element in the semiconductor film therein;  
removing the material having a tensile stress of  $8 \times 10^9$  dynes/cm<sup>2</sup> or more from the semiconductor film;  
forming a gate insulating film over the semiconductor film;  
forming a gate electrode over the gate insulating film.

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62. (New) A method of manufacturing a semiconductor device according to claim 60, wherein said material is formed by LPCVD within a temperature range of between 500 and 900°C.

SUB  
C17 63. (New) A method of manufacturing a semiconductor device according to claim 60, wherein said material is formed by LPCVD within a pressure range of between 0.1 and 3 Torr.

B2  
ent 64. (New) A method of manufacturing a semiconductor device according to claim 60, wherein said material is formed by LPCVD with a gas containing chlorine as a material gas.

65. (New) A method of manufacturing a semiconductor device according to claim 60, wherein said material is a silicon nitride film formed by LPCVD.

66. (New) A method of manufacturing a semiconductor device according to claim 64, wherein a composition ratio of N/Si in said silicon nitride film is between 1.2 and 1.4.